FORM 1449*  O PROPRIATION DISCLOSURE STATEMENT	Docket Number: 10873.1440US01	Application Number: 10/809,033		
N AN APPLICATION	Applicant: SASAKI et al.			
AUG 0 4 2004 (Use several sheets if necessary)	Filing Date: March 25, 2004	Group Art Unit: Unknown		
Chr. Sept.				

		U.S. PATENT DOCUME	NTS				
DOCUMENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIAT		
	FO	REIGN PATENT DOCUM	MENTS		<u> </u>		
DOCUMENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION		
	ļ				YES	NO	
2000-233993	08.2000	Japan			Abstract		
OTHER	DOCUMENT	S (Including Author, Title,	Date, Pertinent P	ages, Etc.)	<u> </u>		
Kurai et a 36 (1997)	I., "Nucleation of the contract of the contrac	Control in the Growth of Bu 5, Part 2, No. 2B, 15 Februa	ılk GaN by Subп гу 1997	nission Method", I	Ipn. J. Appl. Pl	ıys., Vol.	
Nishino et 925.	Nishino et al., "Bulk GaN Growth by Direct Synthesis Method", Journal of Crystal Growth, 237-239 (2002) 9. 925.						
	DOCUMENT NO.  2000-233993  OTHER  Kurai et a 36 (1997)  Nishino et	FOIDOCUMENT NO. DATE  FOIDOCUMENT NO. DATE  2000-233993 08.2000  OTHER DOCUMENT  Kurai et al., "Nucleation of 36 (1997), pp. L184-L186  Nishino et al., "Bulk GaN	FOREIGN PATENT DOCUMENT NO.  DATE  FOREIGN PATENT DOCUMENT NO.  DATE  COUNTRY  2000-233993  08.2000  Japan  OTHER DOCUMENTS (Including Author, Title,  Kurai et al., "Nucleation Control in the Growth of Bu 36 (1997), pp. L184-L186, Part 2, No. 2B, 15 Februa  Nishino et al., "Bulk GaN Growth by Direct Synthesis	FOREIGN PATENT DOCUMENTS  DOCUMENT NO. DATE COUNTRY CLASS  2000-233993 08.2000 Japan ———  OTHER DOCUMENTS (Including Author, Title, Date, Pertinent F  Kurai et al., "Nucleation Control in the Growth of Bulk GaN by Subm 36 (1997), pp. L184-L186, Part 2, No. 2B, 15 February 1997  Nishino et al., "Bulk GaN Growth by Direct Synthesis Method". Journ	FOREIGN PATENT DOCUMENTS  DOCUMENT NO. DATE COUNTRY CLASS SUBCLASS  2000-233993 08.2000 Japan ———  OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)  Kurai et al., "Nucleation Control in the Growth of Bulk GaN by Submission Method", 36 (1997), pp. L184-L186, Part 2, No. 2B, 15 February 1997  Nishino et al., "Bulk GaN Growth by Direct Synthesis Method", Journal of Crystal Gro	DOCUMENT NO. DATE NAME CLASS SUBCLASS FILING IF APPROVED TO THER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)  Kurai et al., "Nucleation Control in the Growth of Bulk GaN by Submission Method", Jpn. J. Appl. Pf 36 (1997), pp. L184-L186, Part 2, No. 2B, 15 February 1997  Nishino et al., "Bulk GaN Growth by Direct Synthesis Method", Journal of Crystal Growth, 237-239 (Nishino et al., "Bulk GaN Growth by Direct Synthesis Method", Journal of Crystal Growth, 237-239 (Nishino et al., "Bulk GaN Growth by Direct Synthesis Method", Journal of Crystal Growth, 237-239 (Nishino et al., "Bulk GaN Growth by Direct Synthesis Method", Journal of Crystal Growth, 237-239 (Nishino et al., "Bulk GaN Growth by Direct Synthesis Method", Journal of Crystal Growth, 237-239 (Nishino et al., "Bulk GaN Growth by Direct Synthesis Method", Journal of Crystal Growth, 237-239 (Nishino et al., "Bulk GaN Growth by Direct Synthesis Method", Journal of Crystal Growth, 237-239 (Nishino et al., "Bulk GaN Growth by Direct Synthesis Method", Journal of Crystal Growth, 237-239 (Nishino et al., "Bulk GaN Growth by Direct Synthesis Method", Journal of Crystal Growth, 237-239 (Nishino et al., "Bulk GaN Growth by Direct Synthesis Method", Journal of Crystal Growth, 237-239 (Nishino et al., "Bulk GaN Growth by Direct Synthesis Method", Journal of Crystal Growth, 237-239 (Nishino et al., "Bulk GaN Growth by Direct Synthesis Method", Journal of Crystal Growth, 237-239 (Nishino et al., "Bulk GaN Growth by Direct Synthesis Method", Journal of Crystal Growth, 237-239 (Nishino et al., "Bulk GaN Growth by Direct Synthesis Method", Journal of Crystal Growth, 237-239 (Nishino et al., "Bulk GaN Growth by Direct Synthesis Method", Journal of Crystal Growth, 237-239 (Nishino et al., "Bulk GaN Growth by Direct Synthesis Method", Journal of Crystal Growth, 237-239 (Nishino et al., "Bulk GaN Growth by Direct Synthesis Method", Journal of Crystal Growth, 237-239 (Nishino et al., "Bulk GaN Growth et al., "Bulk GaN Growth et al., "Bulk GaN Growth et al.	

23552
PATENT TRADEMARK OFFICE

EYAR	<b>IINER</b>	
CXAN	NINER	

DATE CONSIDERED 3-4-6

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form for next communication to the Applicant.

,[	FORM 1449 P SNEOR	MATION DISCLOSURE STATEMENT	Docket Number: 10873.1440US01	Application Number: 10/809,033	
	27 2004 G	IN AN APPLICATION	Applicant: SASAKI et al.		
	25 % mos	(Use several sheets if necessary)	Filing Date: March 25, 2004	Group Art Unit: Unknown	

		U.S. PATENT DOCUMEN	its					
DOCUMENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE			
	<u> </u>							
	<u> </u>							
						<del> – –</del>		
	<del></del>		-	·				
	FOI	REIGN PATENT DOCUM	IENTS		<u></u>			
DOCUMENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION			
					YES	NO		
2004/013385	02.2004	wo						
	-							
-								
OTHER	DOCUMENT	S (Including Author, Title,	Date, Pertinent I	Pages, Etc.)				
Imade et a 48th Sym	Imade et al., "Growth of Bulk GaN Single Crystals by High-Pressure Sublimation Method", Proceedings of the 48th Symposium on Synthetic Crystals, 1 A06, pp 23-24							
Imade et a	al. "Growth of I , Jpn. J. Appl. P	Thick GaN Films with High Phys., Vol. 43 (2004), pp. L4	Growth Rate Us 186-L488	sing Sublimation M	lethod under	High		
	DOCUMENT NO.  2004/013385  OTHER  Imade et a 48th Sym  Imade et a	FOIDOCUMENT NO. DATE  FOIDOCUMENT NO. DATE  2004/013385 02.2004  OTHER DOCUMENT  Imade et al., "Growth of 48th Symposium on Syntaxian Imade et al." Growth of 18th Symposium on Syntaxian Imade et al. "Growth of 18th Symposium on Syntaxian Imade et al." Growth Office Imade et al.	FOREIGN PATENT DOCUMENT NO. DATE COUNTRY  DOCUMENT NO. DATE COUNTRY  2004/013385 02.2004 WO  OTHER DOCUMENTS (Including Author, Title,  Imade et al., "Growth of Bulk GaN Single Crystals b 48th Symposium on Synthetic Crystals, 1 A06, pp 23  Imade et al. "Growth of Thick GaN Films with High	FOREIGN PATENT DOCUMENTS  DOCUMENT NO. DATE COUNTRY CLASS  2004/013385 02.2004 WO ——  OTHER DOCUMENTS (Including Author, Title, Date, Pertinent I Imade et al., "Growth of Bulk Gan Single Crystals by High-Pressure 48th Symposium on Synthetic Crystals, 1 A06, pp 23-24	FOREIGN PATENT DOCUMENTS  DOCUMENT NO. DATE COUNTRY CLASS SUBCLASS  2004/013385 02.2004 WO ————  OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)  Imade et al., "Growth of Bulk GaN Single Crystals by High-Pressure Sublimation Meth 48th Symposium on Synthetic Crystals, 1A06, pp 23-24  Imade et al. "Growth of Thick GaN Films with High Growth Rate Using Sublimation Meth	DOCUMENT NO. DATE NAME CLASS SUBCLASS FILING IF APPROVED THE POCUMENT SUBCLASS OF TRANS  OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)  Imade et al., "Growth of Bulk GaN Single Crystals by High-Pressure Sublimation Method", Proceeding 48th Symposium on Synthetic Crystals, 1 A06, pp 23-24  Imade et al. "Growth of Thick GaN Films with High Growth Rate Using Sublimation Method under the proceeding the process of the process of the proceeding the process of the proceeding the process of the		

23552
PATENT TRADEMARK OFFICE

	<u>-Δ</u>	1/				 	
EXAMINER	$\square$		DATE CONSIDERED	3-	4-6		

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form for next communication to the Applicant.